iC-LF1401

128x1 LINEAR IMAGE SENSOR

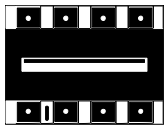
FEATURES

- 128 active photo pixels of 56 µm at a 63.5 µm pitch (400 DPI)
- Integrating L-V conversion followed by a sample & hold circuit
- High sensitivity and uniformity over wavelength
- High clockrates of up to 5 MHz
- Only 128 clocks required for readout
- Shutter function enables flexible integration times
- Glitch-free analogue output
- Push-pull output amplifier
- 5 V single supply operation
- Can run off external bias to reduce power consumption
- Pin-to-pin compatible with TSL1401

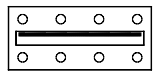
APPLICATIONS

- Optical line image sensors
- CCD substitute

PACKAGES



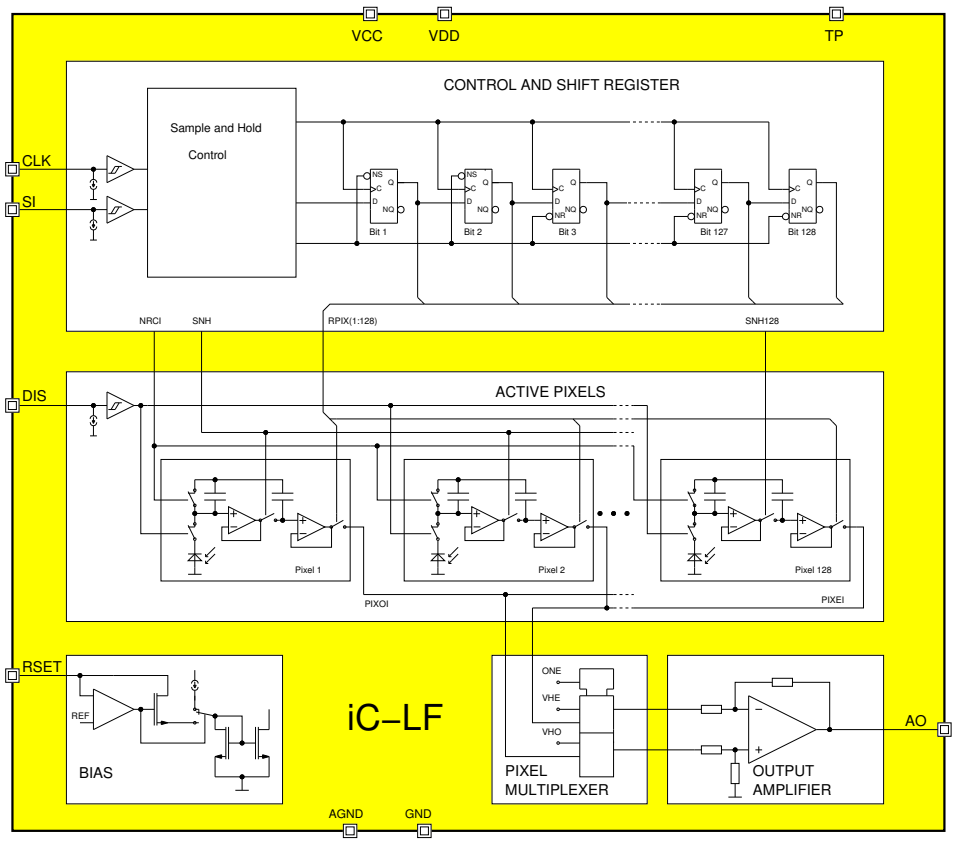
OLGA LF2C



OBGA™ LF3C

Die size (8.5 mm x 1.6 mm)

BLOCK DIAGRAM



DESCRIPTION

iC-LF1401 is an integrating light-to-voltage converter with a line of 128 pixels pitched at 63.5 µm (center-to-center distance). Each pixel consists of a 56.4 µm x 200 µm photodiode and an integration capacitor with a sample-and-hold circuit.

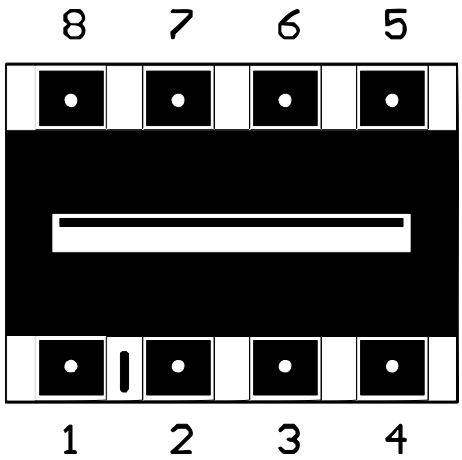
The integrated control logic makes operation very simple, with only a start and clock signal necessary. A third control input (DIS) enables the integration to be suspended at any time (electronic shutter).

When the start signal is given hold mode is activated for all pixels simultaneously with the next leading clock edge; starting with pixel 1 the hold voltages are switched in sequence to the push-pull output amplifier. The second clock pulse resets all integration capacitors and the integration period starts again in the background during the output phase. A run is complete after 128 clock pulses.

iC-LF1401 is suitable for high clock rates of up to 5 MHz. If this is not required the supply current can be reduced via the external bias setting (current into pin RSET).

PACKAGES OLGA LF2C, OBGA™ LF3C

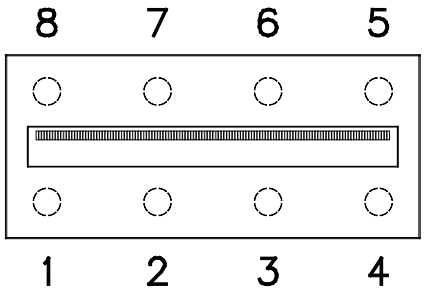
PIN CONFIGURATION OLGA LF2C



PIN FUNCTIONS

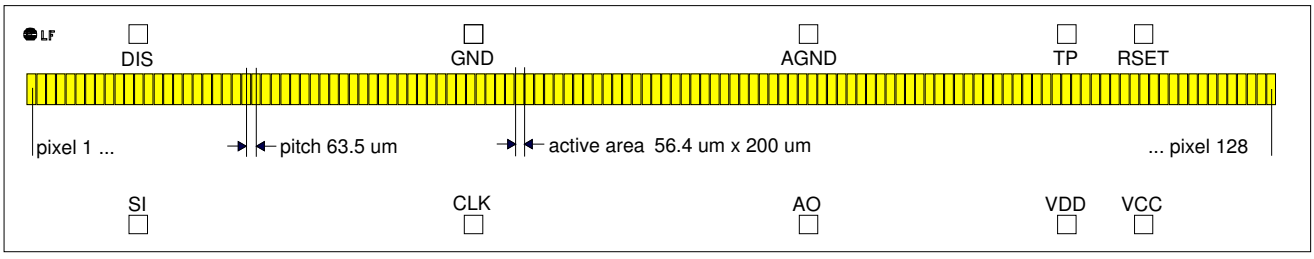
No.	Name	Function
1	SI	Start Integration Input
2	CLK	Clock Input
3	AO	Analogue Output
4	VCC	+5 V Supply Voltage
5	RSET	Bias Current (connected to GND for internal bias = default; resistor from VCC to RSET for reduced current consumption)
6	AGND	Analogue Ground
7	GND	Digital Ground
8	DIS	Hold Integration Input

PIN CONFIGURATION OBGA™ LF3C



CHIP LAYOUT

Die size: 8.5 mm x 1.6 mm



ABSOLUTE MAXIMUM RATINGS

Beyond these values damage may occur; device operation is not guaranteed.

Item No.	Symbol	Parameter	Conditions	Min.	Max.	Unit
G001	VDD	Digital Supply Voltage		-0.3	6	V
G002	VCC	Analog Supply Voltage		-0.3	6	V
G003	V()	Voltage at SI, CLK, DIS, RSET, TP, AO		-0.3	VCC + 0.3	V
G004	I()	Current in RSET, TP, AO		-10	10	mA
G005	Vd()	ESD Susceptibility at all pins	MIL-STD-883, Method 3015, HBM 100 pF discharged through 1.5 kΩ		2	kV
G006	Tj	Operating Junction Temperature		-40	125	°C
G007	Ts	Storage Temperature Range	see package specification			

THERMAL DATA

Operating Conditions: VCC = VDD = 5 V ±10 %

Item No.	Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
T01	Ta	Operating Ambient Temperature Range (extended range on request)	see package specification				

All voltages are referenced to ground unless otherwise stated.
All currents into the device pins are positive; all currents out of the device pins are negative.

ELECTRICAL CHARACTERISTICS

Operating Conditions: VCC = VDD = 5 V ±10 %, RSET = GND, Tj = -25...85 °C unless otherwise noted

Item No.	Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
Total Device							
001	VDD	Digital Supply Voltage Range		4.5		5.5	V
002	VCC	Analog Supply Voltage Range		4.5		5.5	V
003	I(VDD)	Supply Current in VDD	f(CLK) = 1 MHz		200	300	µA
004	I(VCC)	Supply Current in VCC			8	13	mA
005	Vc()hi	Clamp Voltage hi at SI, CLK,DIS, TP, RSET	Vc()hi = V() − V(VCC); I() = 1 mA	0.3		1.8	V
006	Vc()lo	Clamp Voltage lo at SI, CLK,DIS, TP, RSET	Vc()hi = V() − V(AGND); I() = -1 mA	-1.5		-0.3	V
007	Vc()hi	Clamp Voltage hi at AO	Vc()hi = V(AO) − V(VCC); I(AO) = 1 mA	0.3		1.5	V
008	Vc()lo	Clamp Voltage lo at AO, VCC, VDD, GND	Vc()lo = V() − V(AGND); I() = -1 mA	-1.5		-0.3	V
Photodiode Array							
201	A()	Radiant Sensitive Area	200 µm x 56.40 µm per Pixel		0.01128		mm²
202	S(λ)max	Spectral Sensitivity	λ = 680 nm		0.5		A/W
203	λar	Spectral Application Range	S(λar) = 0.25 x S(λ)max	400		980	nm
Analogue Output AO							
301	Vs()lo	Saturation Voltage lo	I() = 1 mA			0.5	V
302	Vs()hi	Saturation Voltage hi	Vs()hi = VCC − V(), I() = -1 mA			1	V
303	K	Sensitivity	λ = 680 nm, package OLGA LF2C		2.88		V/pWs
304	V0()	Offset Voltage	integration time 1 ms, no illumination		400	800	mV
305	ΔV0()	Offset Voltage Deviation during integration mode	ΔV0() = V(AO)t1 − V(AO)t2, Δt = t2 − t1 = 1 ms	-250		50	mV
306	ΔV()	Signal Deviation during hold mode	ΔV() = V(AO)t1 − V(AO)t2, Δt = t2 − t1 = 1 ms	-150		150	mV
307	tp(CLK-AO)	Settling Time	Cl(AO) = 10 pF, CLK lo → hi until V(AO) = 0.98 x V(VCC)			200	ns
308	PRNU	Pixel Response Nonuniformity	V(AO) = 2 V			±5*	%
309	INL	Integral Nonlinearity	V(AO) = 1...3.5 V		±1		%
310	V_{noise}(AO)	Output Noise Voltage	V(AO) = 2 V		2		mV_{RMS}
311	DR	Dynamic Range†	$V(AO)_{max}$ = 3.5 V		62		dB
Power-On Reset							
801	VCCon	Power-On Release by VCC				4.4	V
802	VCCoff	Power-Down Reset by VCC		1			V
803	VCChys	Hysteresis	VCChys = VCCon − VCCoff	0.4	1	2	V
Bias Current Adjust RSET							
901	Ibias()	Permissible External Bias Current		20		100	µA
902	Vref	Reference Voltage	I(RSET) = Ibias	2.5	3	3.5	V
Input Interface SI, CLK, DIS							
B01	Vt()hi	Threshold Voltage hi	see Fig. 2	1.4		1.8	V
B02	Vt()lo	Threshold Voltage lo	see Fig. 2	0.9		1.2	V
B03	Vt()hys	Hysteresis	Vt()hys = Vt()hi − Vt()lo, see Fig. 2	300		800	mV
B04	I()	Pull-Down Current		10	30	50	µA
B05	fclk	Permissible Clock Frequency				5	MHz

* Projected values by sample characterization

† $DR = 20 \times log \frac{V(AO)_{max} - V0(AO)_{max}}{V_{noise}(AO)}$

OPTICAL CHARACTERISTICS: Diagrams

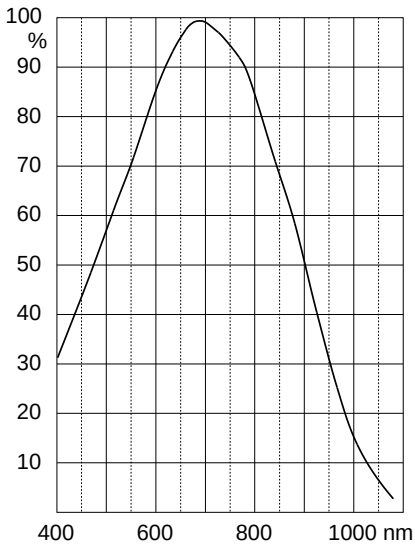


Figure 1: Relative spectral sensitivity

OPERATING REQUIREMENTS: Logic

Operating Conditions: VCC = VDD = 5 V ±10 %, Tj = -25...85 °C
input levels lo = 0...0.45 V, hi = 2.4 V...VCC, see Fig. 2 for reference levels

Item No.	Symbol	Parameter	Conditions	Fig.	Min.	Max.	Unit
I001	tset	Setup Time: SI stable before CLK lo → hi		3	50		ns
I002	thold	Hold Time:SI stable after CLK lo → hi		3	50		ns

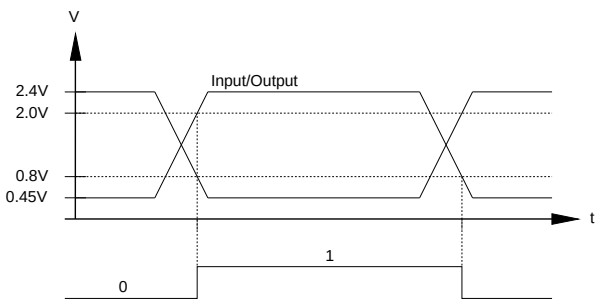


Figure 2: Reference levels

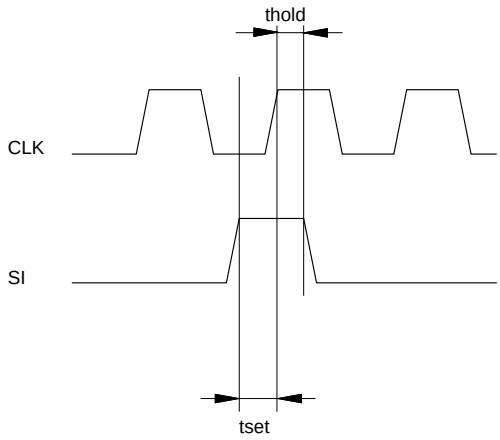


Figure 3: Timing diagram

DESCRIPTION OF FUNCTIONS

Normal operation
Following an internal power-on reset the integration and hold capacitors are discharged and the sample and hold circuit is set to sample mode. A high signal at SI and a rising edge at CLK triggers a readout cycle and with it a new integration cycle.

In this process the hold capacitors of pixels 1 to 127 are switched to hold mode immediately (SNH = 1), with pixel 128 (SNH128 = 1) following suit one clock pulse later. This special procedure allows all pixels to be read out with just 128 clock pulses. The integration capacitors are discharged by a one clock long reset signal (NRCI = 0) which occurs between the 2nd and 3rd falling edge of the readout clock pulse (cf. Figure 4). After the 127 pixels have been read out these are again set to sample mode (SNH = 0), likewise for pixel 128 one clock pulse later (SNH128 = 0).

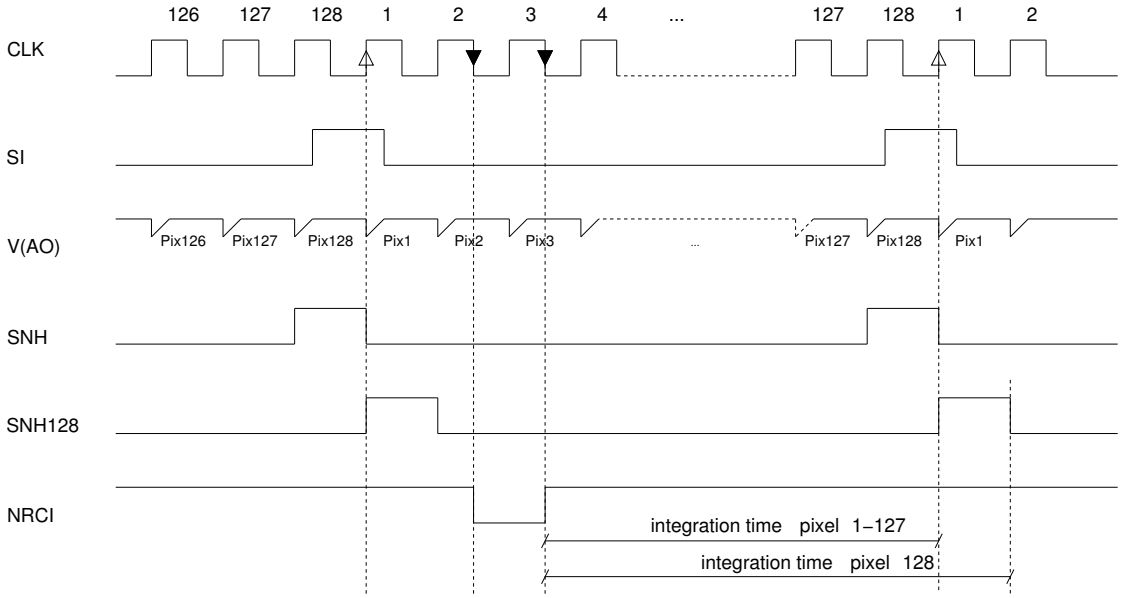


Figure 4: Readout cycle and integration sequence

If prior to the 128th clock pulse a high signal occurs at SI the present readout is halted and immediately reinitiated with pixel 1. In this instance the hold capacitors retain their old value i.e. hold mode prevails (SNH/SNH128 = 0).

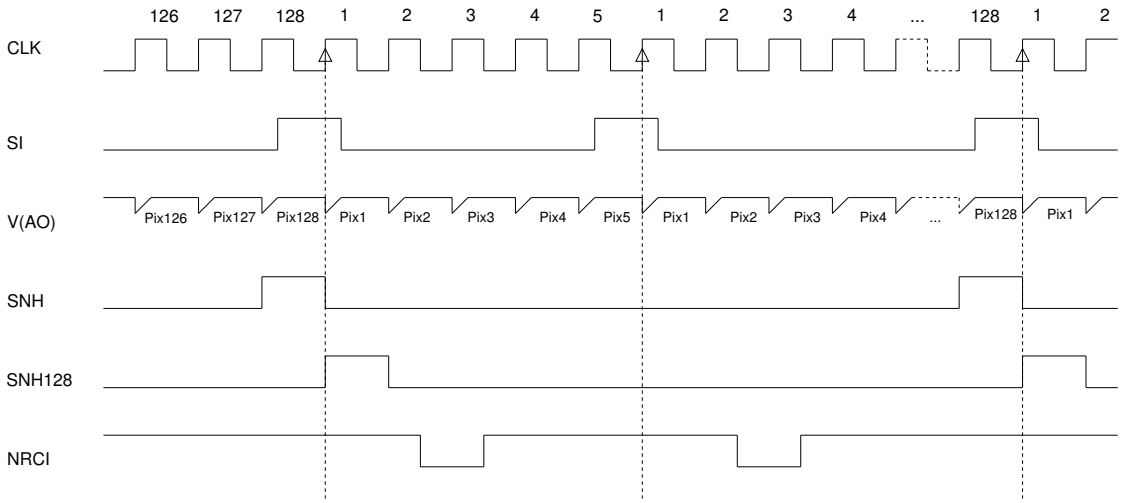


Figure 5: Restarting a readout cycle

With more than 128 clock pulses until the next SI signal, pixel 1 is output without entering hold mode; the output voltage tracks the voltage of the pixel 1 integration capacitor.

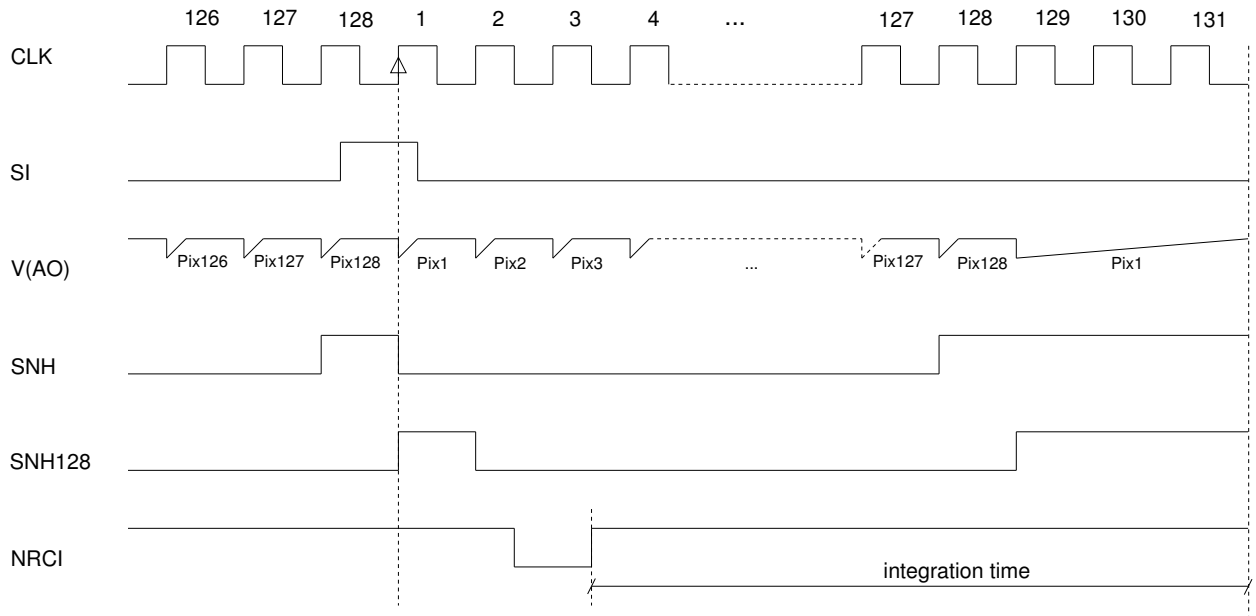


Figure 6: Clock pulse continued without giving a new integration start signal

Operation with the shutter function
Integration can be suspended at any time via pin DIS, i.e. the photodiodes are disconnected from their corresponding integration capacitor when DIS is high and the current integration capacitor voltages are maintained. If this pin is open or switched to GND the pixel photocurrents are summed up by the integration capacitors until the next successive SI signal follows.

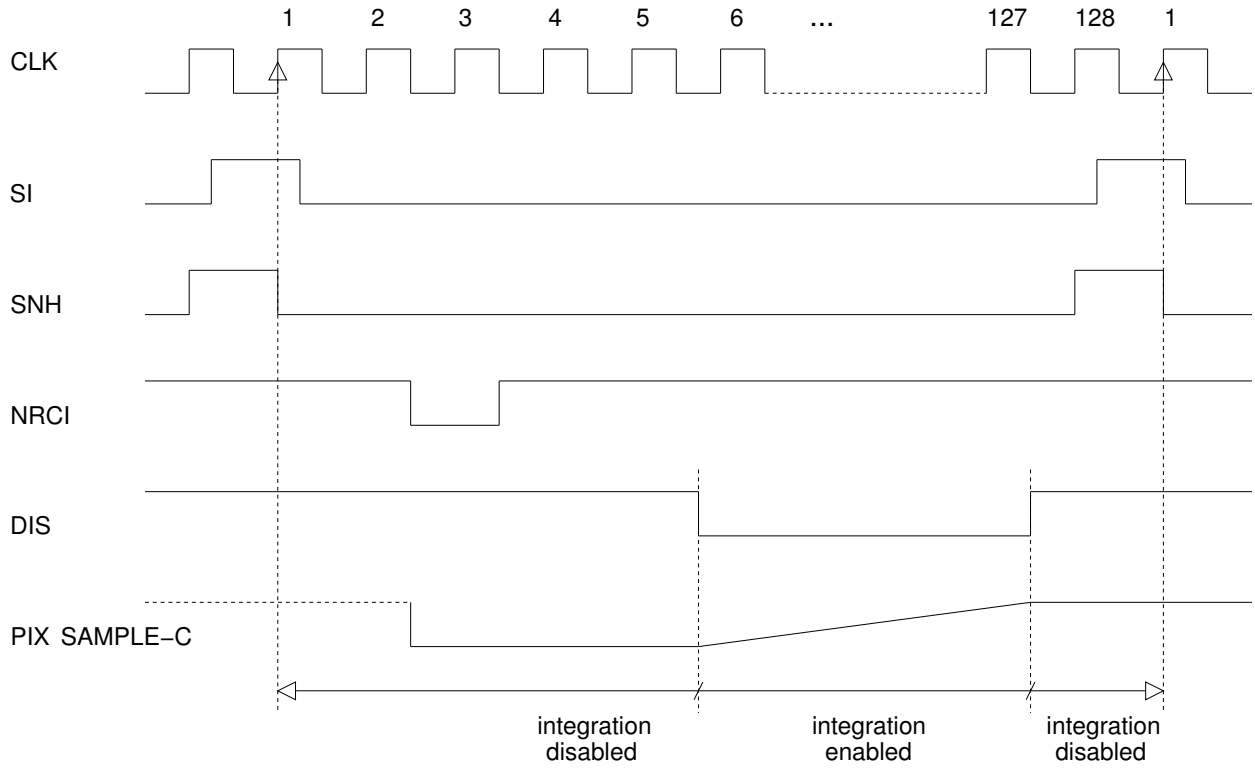


Figure 7: Defining the integration time via shutter input DIS

External bias current setting

In order to reduce the power consumption of the device an external reference current can be supplied to pin RSET which reduces the maximum readout frequency, however. To this end a resistor must be connected from VCC to RSET. If this pin is not used, it should be connected to GND.

ORDERING INFORMATION

Type	Package	Order Designation
iC-LF	OLGA LF2C OBGA™ LF3C -	iC-LF OLGA LF2C iC-LF OBGA LF3C iC-LF chip

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Appointed local distributors: http://www.ichaus.de/support_distributors.php